

Bias Resistor Transistor NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

● FEATURES

- 1)Simplifies Circuit Design
- 2)Reduces Board Space and Component Count
- 3)We declare that the material of product compliant with
- RoHS requirements and Halogen Free.
- 4)S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMUN2212LT1G	A8B	3000/Tape&Reel
LMUN2212LT3G	A8B	10000/Tape&Reel

●MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	VCBO	50	V
Collector-Emitter Voltage	VCEO	50	V
Collector Current	IC	100	mA
Total Power Dissipation	PD		
@ Ta = 25°C(Note 1.)		246	mW
Derate above 25°C		1.5	°C/W

LMUN2212LT1G S-LMUN2212LT1G



●THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Thermal Resistance – Junction-to-Ambient (Note 1.)	Reja	508	°C/W
Operating and Storage Temperature Range	Topr, Tstg	–55 to +150	°C
Maximum Temperature for Soldering Purposes, Time in Solder Bath	T∟	260 10	°C Sec

●ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS						
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base Cutoff Current	ICBO	_		100	nA	VCB = 50 V, IE = 0
Collector-Emitter Cutoff Current	ICEO	_	-	500	nA	VCE = 50 V, IB = 0
Emitter-Base Cutoff Current	IEBO	_	Ι	0.2	mA	VEB = 6.0 V, IC = 0
Collector-Base Breakdown Voltage	V(BR)CBO	50	-	-	V	IC = 10 μA, IE = 0
Collector-Emitter Breakdown Voltage	V(BR)CEO	50	-	-	V	IC = 2.0 mA, IB = 0
ON CHARACTERISTICS(Note2.)						
DC Current Gain	hFE	60	100	-		VCE = 10 V, IC = 5.0 mA
Collector-Emitter Saturation Voltage	VCE(sat)	_	-	0.25	V	IC = 10 mA, IB = 0.3 mA
						VCC = 5.0 V, VB = 2.5 V, RL =
Output Voltage (on)	VOL	_	_	0.2	V	1.0 k Ω
						VCC = 5.0 V, VB = 0.5 V, RL =
Output Voltage (off)	Vон	4.9	_	-	V	1.0 k Ω
Input Resistor	R1	15.4	22	28.6	k Ω	
Resistor Ratio	R1/R2	0.8	1	1.2		

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%.



LMUN2212LT1G,S-LMUN2212LT1G



ELECTRICAL CHARACTERISTIC CURVES



Figure 2. DC Current Gain



Figure 1. Collector Emitter Saturation Voltage

Figure 3. Output Capacitance



Figure 4. Output Current vs. Input Voltage



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ELECTRICAL CHARACTERISTIC CURVES

Figure 5. Input Voltage vs Output Current



LMUN2212LT1G,S-LMUN2212LT1G

SOT-23



1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982



ми	IN	ICHES	MILLIMETERS		
	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
к	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
v	0.0177	0.0236	0.45	0.60	







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